isc Silicon NPN Pow Transistor — 2SC2655

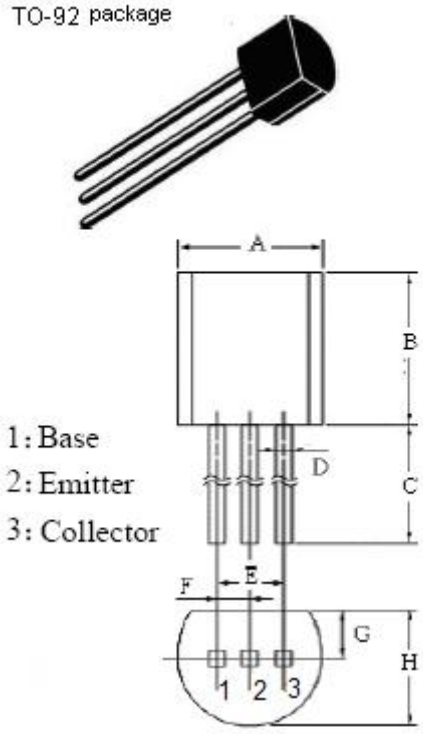
DESCRIPTION

- Silicon NPN epitaxial type
- Low saturation voltage
- Complementary to 2SA1020
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications
- Power switching applications

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0. 92	1. 12
H	3.40	3.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
P_C	Collector Power Dissipation @T_C=25℃	0.9	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A ; I_B= 50mA			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1A ; I_B= 50mA			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 50V; I_E= 0			1	μA
h_{FE-1}	DC Current Gain	I_C= 0.5A ; V_{CE}= 2V	70		240	
h_{FE-2}	DC Current Gain	I_C= 1.5A ; V_{CE}= 2V	40			
f_T	Current-Gain—Bandwidth Product	I_C= 500mA ; V_{CE}= 2V		100		MHz